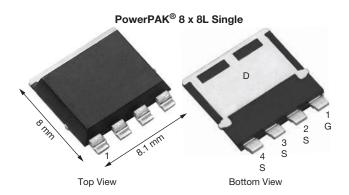


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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



| PRODUCT SUMMARY | | | | | |
|---|-----------------|--|--|--|--|
| V _{DS} (V) | 40 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.00172 | | | | |
| I _D (A) | 200 | | | | |
| Configuration | Single | | | | |
| Package | PowerPAK 8 x 8L | | | | |

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE

N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS | $(T_C = 25 ^{\circ}C, \text{unles})$ | s otherwise noted |) | | |
|--|--|-------------------|------|-----|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Drain-source voltage | | V_{DS} | 40 | V | |
| Gate-source voltage | | V_{GS} | ± 20 | 1 v | |
| Continuous drain current | T _C = 25 °C ^a | I _D | 200 | | |
| Continuous drain current | Continuous drain current T _C = 125 °C | | | | |
| Continuous source current (diode conduction) | | I _S | 136 | Α | |
| Pulsed drain current ^b | I _{DM} | 600 | | | |
| Single pulse avalanche current L = 0.1 mH | | I _{AS} | 85 | | |
| Single pulse avalanche energy | E _{AS} | 361 | mJ | | |
| Maximum power dissipation | T _C = 25 °C | р | 150 | W | |
| Maximum power dissipation | T _C = 125 °C | P_{D} | 50 | VV | |
| Operating junction and storage temperature ran | T _J , T _{stg} | -55 to +175 | °C | | |
| Soldering recommendations (peak temperature) | | 260 | J | | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|-------------|------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-ambient | PCB mount c | R_{thJA} | 50 | °C/W |
| Junction-to-case (drain) | | R_{thJC} | 1 | G/VV |

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|----------------------------|---|---|------|---------|---------|------|
| Static | | | | | • | | |
| Drain-source breakdown voltage | V _{DS} | V_{GS} | = 0, I _D = 250 μA | 40 | - | - | V |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = | = V _{GS} , I _D = 250 μA | 2.5 | 3 | 3.5 | V |
| Gate-source leakage | I _{GSS} | V _{DS} = | 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V | - | - | 1 | |
| Zero gate voltage drain current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 125 °C | - | - | 50 | μΑ |
| | | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 175 °C | - | - | 150 | |
| On-state drain current a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 \text{ V}$ | 100 | - | - | Α |
| | | V _{GS} = 10 V | I _D = 20 A | - | 0.00133 | 0.00172 | |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 20 A, T _J = 125 °C | - | - | 0.00273 | Ω |
| | | V _{GS} = 10 V | I _D = 20 A, T _J = 175 °C | - | - | 0.00330 | |
| Forward transconductance b | 9 _{fs} | V _{DS} = 15 V, I _D = 20 A | | - | 160 | - | S |
| Dynamic ^b | | | | | | | |
| Input capacitance | C _{iss} | | | - | 11 770 | 16 480 | |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$ | - | 1255 | 1760 | рF |
| Reverse transfer capacitance | C _{rss} | | | - | 395 | 555 | |
| Total gate charge ^c | Qg | | | - | 175 | 270 | |
| Gate-source charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 20 \text{ V}, I_{D} = 40 \text{ A}$ | - | 46 | - | nC |
| Gate-drain charge c | Q_{gd} | | | - | 27 | - | |
| Gate resistance | R_g | | f = 1 MHz | 0.55 | 0.91 | 1.45 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 22 | 31 | |
| Rise time ^c | t _r | V _{DD} = | = 20 V, $R_L = 0.5 \Omega$ | - | 23 | 33 | 200 |
| Turn-off delay time ^c | t _{d(off)} | $I_D \cong 40 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | | - | 58 | 81 | ns |
| Fall time ^c | t _f | | | - | 8 | 21 | |
| Source-Drain Diode Ratings and Cha | aracteristics ^b | | | | | | |
| Reverse recovery time | t _{rr} | V _{DD} = 32 V, I _{FM} = 40 A, di/dt = 100 A/µs | | - | 75 | - | ns |
| Reverse recovery charge | Q _{rr} | | | - | 0.16 | - | nC |
| Reverse recovery current | I _{RM} | | , ατ = 100 / V μο | - | - | -4.6 | Α |
| Pulsed current ^a | I _{SM} | | | - | - | 450 | Α |
| Forward voltage | V_{SD} | $I_F = 50 \text{ A}, V_{GS} = 0$ | | - | 0.82 | 1.2 | V |

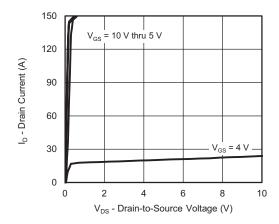
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

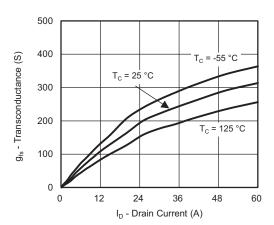
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



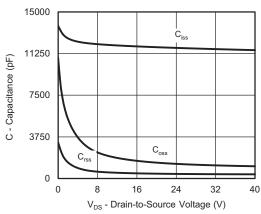
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



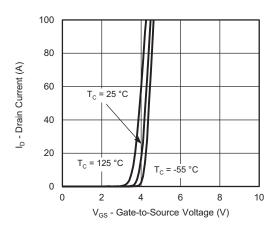
Output Characteristics



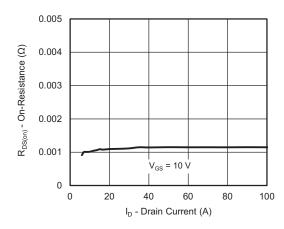
Transconductance



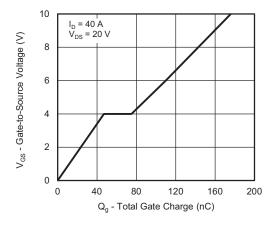
Capacitance



Transfer Characteristics



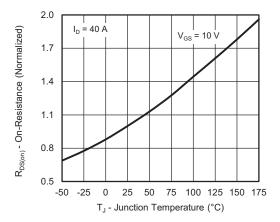
On-Resistance vs. Drain Current



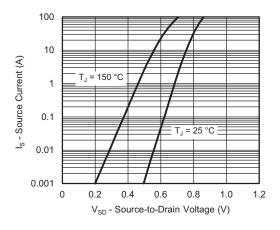
Gate Charge



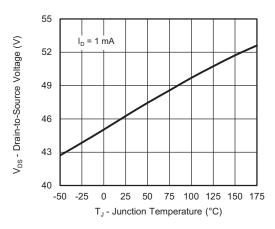
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



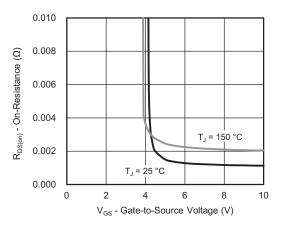
On-Resistance vs. Junction Temperature



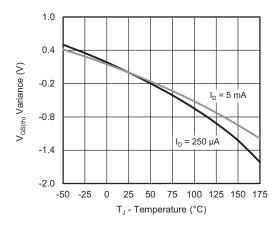
Source Drain Diode Forward Voltage



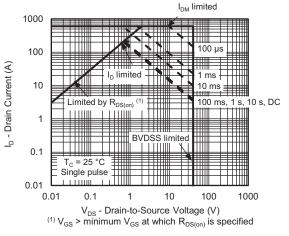
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



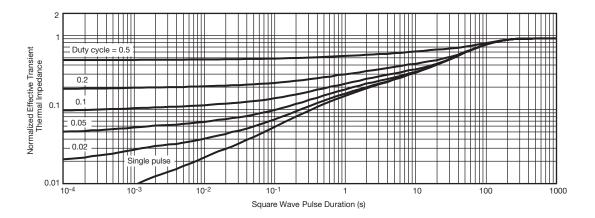
Threshold Voltage



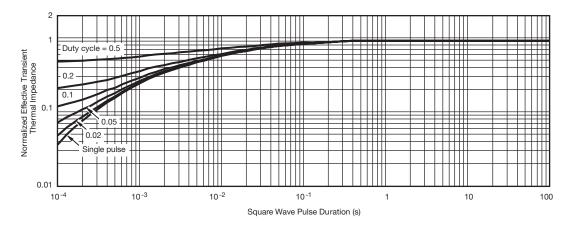
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

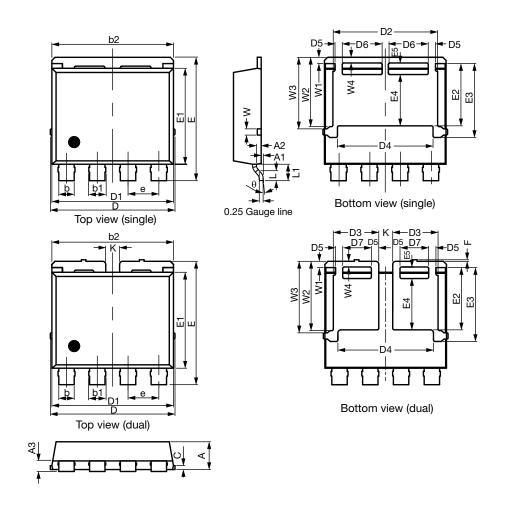


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76570.



PowerPAK® 8 x 8L Case Outline



| DIM. | MILLIMETERS | | | INCHES | | |
|------|-------------|------|------|--------|-------|-------|
| DIM. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| Α | 1.70 | 1.80 | 1.90 | 0.067 | 0.071 | 0.075 |
| A1 | 0.00 | 0.08 | 0.13 | 0.000 | 0.003 | 0.005 |
| A2 | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| A3 | 0.55 | 0.62 | 0.70 | 0.022 | 0.024 | 0.028 |
| b | 0.92 | 1.00 | 1.08 | 0.036 | 0.039 | 0.043 |
| b1 | 1.02 | 1.10 | 1.18 | 0.040 | 0.043 | 0.046 |
| b2 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 |
| D | 8.00 | 8.10 | 8.25 | 0.315 | 0.319 | 0.325 |
| D1 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 |
| D2 | 6.70 | 6.80 | 6.90 | 0.264 | 0.268 | 0.272 |
| D3 | 2.85 | 2.95 | 3.05 | 0.112 | 0.116 | 0.120 |
| D4 | 6.11 | 6.21 | 6.31 | 0.241 | 0.244 | 0.248 |
| D5 | 0.37 | 0.47 | 0.57 | 0.015 | 0.019 | 0.022 |
| D6 | 2.49 | 2.59 | 2.69 | 0.098 | 0.102 | 0.106 |
| D7 | 1.76 | 1.86 | 1.96 | 0.069 | 0.073 | 0.077 |

Revision: 16-Oct-17 1 Document Number: 67734



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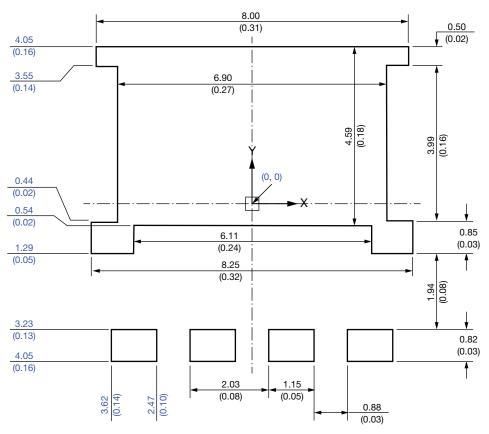
| DIM. | | MILLIMETERS | | INCHES | | | |
|------|------|-------------|------|--------|-------|-------|--|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| е | 1.95 | 2.00 | 2.05 | 0.077 | 0.079 | 0.081 | |
| E | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 | |
| E1 | 6.12 | 6.22 | 6.32 | 0.241 | 0.245 | 0.249 | |
| E2 | 3.94 | 4.04 | 4.14 | 0.140 | 0.159 | 0.163 | |
| E3 | 4.69 | 4.79 | 4.89 | 0.185 | 0.189 | 0.193 | |
| E4 | 3.23 | 3.33 | 3.43 | 0.127 | 0.131 | 0.135 | |
| E5 | 0.65 | 0.75 | 0.85 | 0.026 | 0.030 | 0.033 | |
| F | 0.00 | 0.10 | 0.15 | 0.000 | 0.004 | 0.006 | |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 | |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 | |
| K | 0.80 | 0.90 | 1.00 | 0.031 | 0.035 | 0.039 | |
| W | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| W1 | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| W2 | 4.39 | 4.49 | 4.59 | 0.173 | 0.177 | 0.181 | |
| W3 | 4.54 | 4.64 | 4.74 | 0.179 | 0.183 | 0.187 | |
| W4 | 0.32 | 0.37 | 0.42 | 0.013 | 0.015 | 0.017 | |
| θ | 6° | 10° | 14° | 6° | 10° | 14° | |

C17-1388-Rev. B, 16-Oct-17

DWG: 6026



Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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